

NP82N10PUF

R07DS0444EJ0100

Rev.1.00

Aug 26, 2011

MOS FIELD EFFECT TRANSISTOR

Description

The NP82N10PUF is N-channel MOS Field Effect Transistor designed for high current switching applications.

Features

- Super low on-state resistance
— $R_{DS(on)} = 15 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 10 \text{ V}$, $I_D = 41 \text{ A}$)
- Low C_{iss} : $C_{iss} = 2900 \text{ pF TYP.}$ ($V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text{ V}$)
- Designed for automotive application and AEC-Q101 qualified

Ordering Information

Part No.	Lead Plating	Packing		Package
NP82N10PUF-E1-AY ^{*1}	Pure Sn (Tin)	Tape 800 p/reel	Taping (E1 type)	TO-263 (MP-25ZP)
NP82N10PUF-E2-AY ^{*1}			Taping (E2 type)	

Note: *1. Pb-free (This product does not contain Pb in the external electrode.)

Absolute Maximum Ratings (T_A = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	100	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±20	V
Drain Current (DC) (T _C = 25°C)	I _{D(DC)}	±82	A
Drain Current (pulse) *1	I _{D(pulse)}	±164	A
Total Power Dissipation (T _C = 25°C)	P _{T1}	150	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	1.8	W
Channel Temperature	T _{ch}	175	°C
Storage Temperature	T _{stg}	-55 to +175	°C
Single Avalanche Current *2	I _{AS}	34	A
Single Avalanche Energy *2	E _{AS}	117	mJ

Thermal Resistance

Channel to Case Thermal Resistance	R _{th(ch-C)}	1.00	°C/W
Channel to Ambient Thermal Resistance *2	R _{th(ch-A)}	83.3	°C/W

Notes: *1. T_C = 25°C, PW ≤ 10 μs, Duty Cycle ≤ 1%

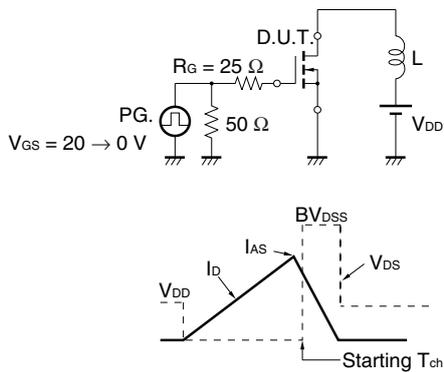
*2. T_{ch(start)} = 25°C, V_{DD} = 50 V, R_G = 25 Ω, L = 100 μH, V_{GS} = 20 V → 0 V

Electrical Characteristics (T_A = 25°C)

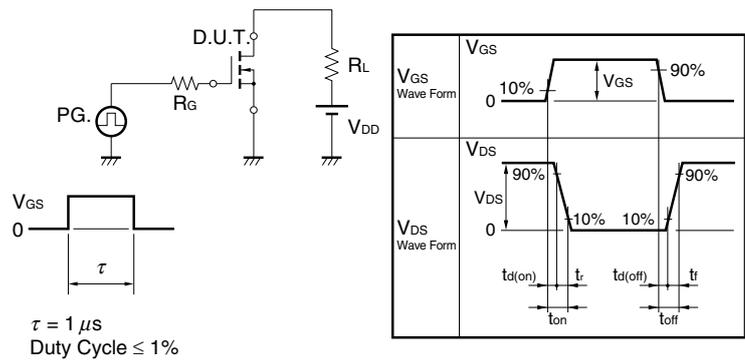
Item	Symbol	MAX.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} = 100 V, V _{GS} = 0 V
Gate Leakage Current	I _{GSS}			±100	nA	V _{GS} = ±20 V, V _{DS} = 0 V
Gate to Source Threshold Voltage	V _{GS(th)}	1.7	2.5	3.3	V	V _{DS} = V _{GS} , I _D = 250 μA
Forward Transfer Admittance *1	y _{fs}	30	60		S	V _{DS} = 5.0 V, I _D = 41 A
Drain to Source On-state Resistance *1	R _{DS(on)1}		12	15	mΩ	V _{GS} = 10 V, I _D = 41 A
	R _{DS(on)2}		13	22	mΩ	V _{GS} = 5.8 V, I _D = 18 A
Input Capacitance	C _{iss}		2900	4350	pF	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz
Output Capacitance	C _{oss}		340	510	pF	
Reverse Transfer Capacitance	C _{rss}		140	250	pF	
Turn-on Delay Time	t _{d(on)}		16	35	ns	V _{DD} = 50 V, I _D = 41 A, V _{GS} = 10 V R _G = 0 Ω
Rise Time	t _r		16	40	ns	
Turn-off Delay Time	t _{d(off)}		60	120	ns	
Fall Time	t _f		8	20	ns	
Total Gate Charge	Q _G		64	96	nC	V _{DD} = 80 V, V _{GS} = 10 V, I _D = 82 A
Gate to Source Charge	Q _{GS}		12		nC	
Gate to Drain Charge	Q _{GD}		22		nC	
Body Diode Forward Voltage *1	V _{F(S-D)}		0.95	1.5	V	I _F = 82 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}		62		ns	I _F = 82 A, V _{GS} = 0 V, di/dt = 100 A/μs
Reverse Recovery Charge	Q _{rr}		135		nC	

Note: *1. Pulsed test

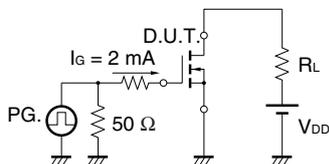
TEST CIRCUIT 1 AVALANCHE CAPABILITY



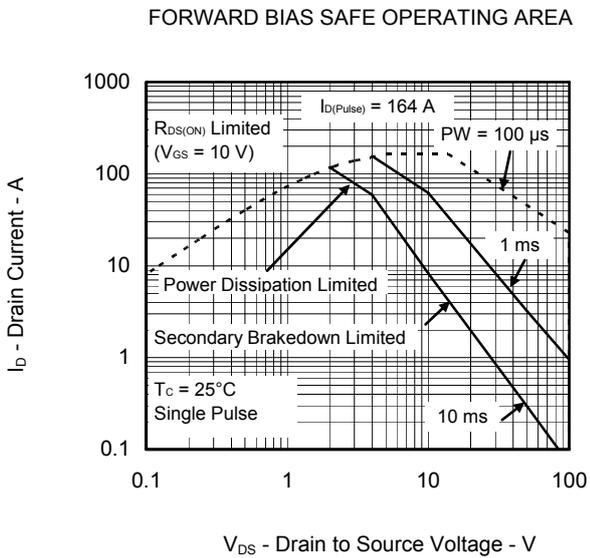
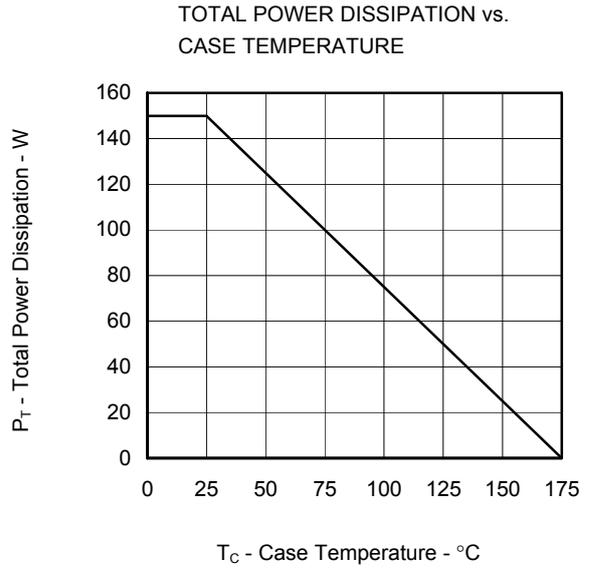
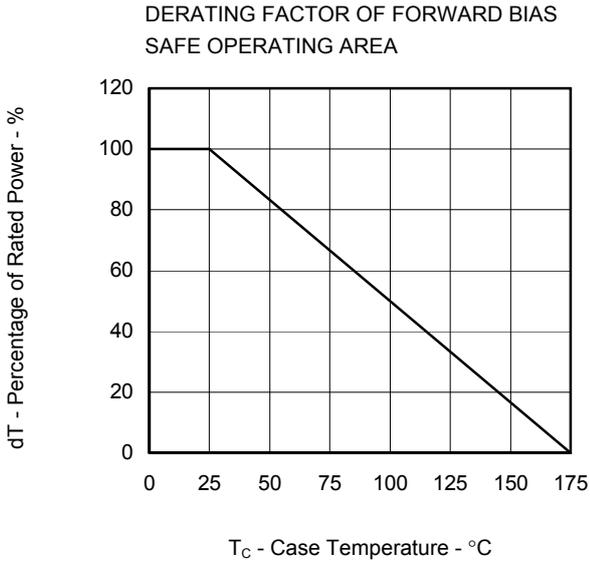
TEST CIRCUIT 2 SWITCHING TIME



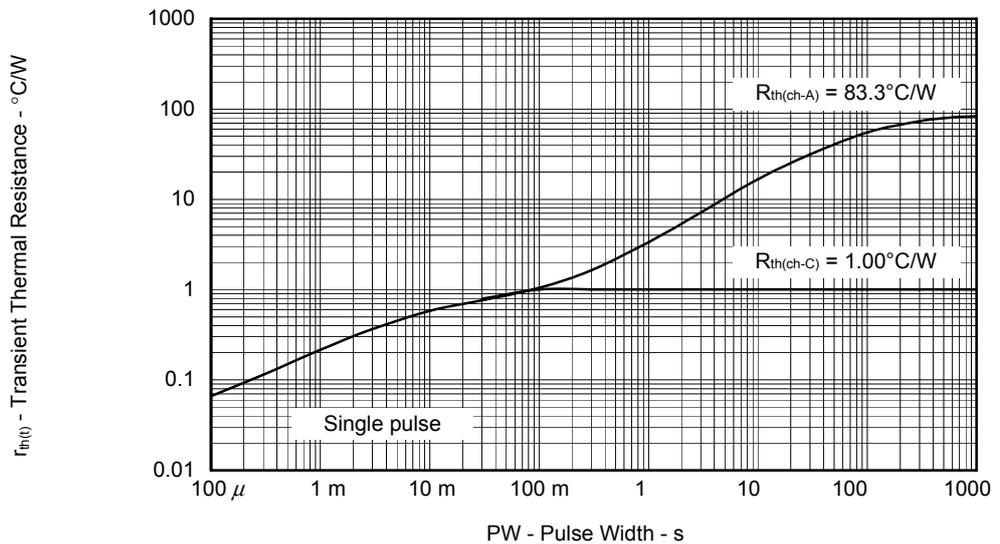
TEST CIRCUIT 3 GATE CHARGE



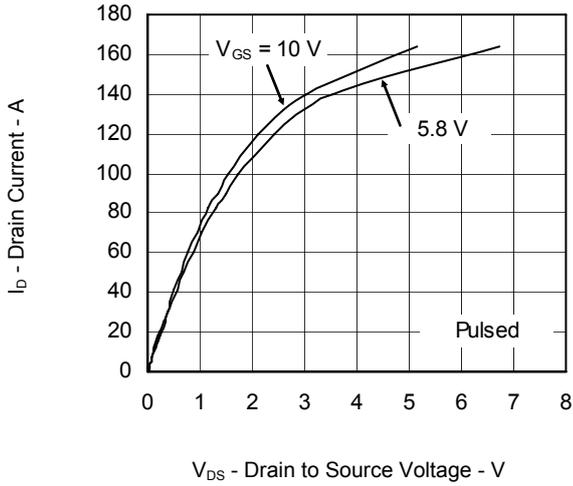
Typical Characteristics (T_A = 25°C)



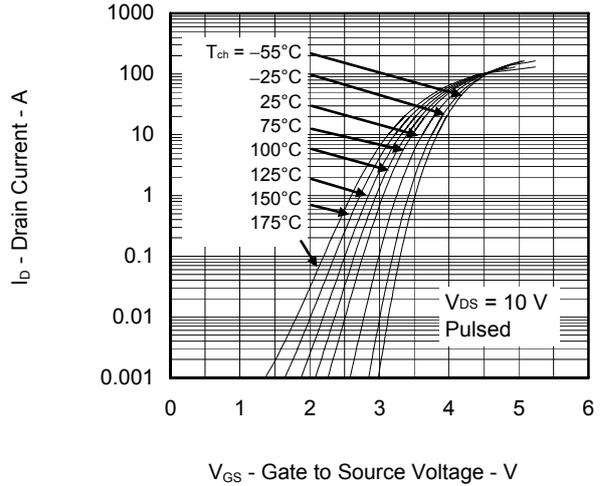
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



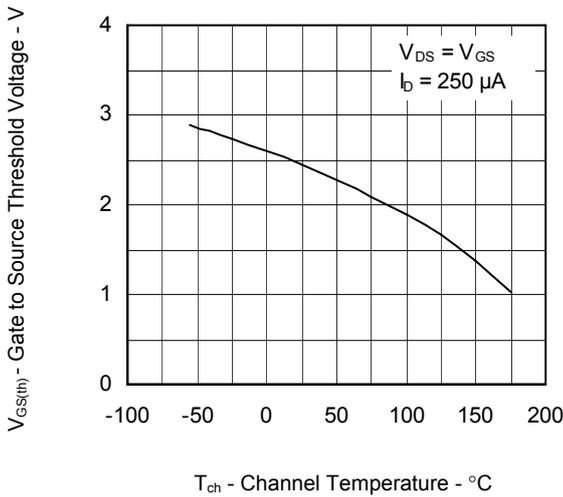
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



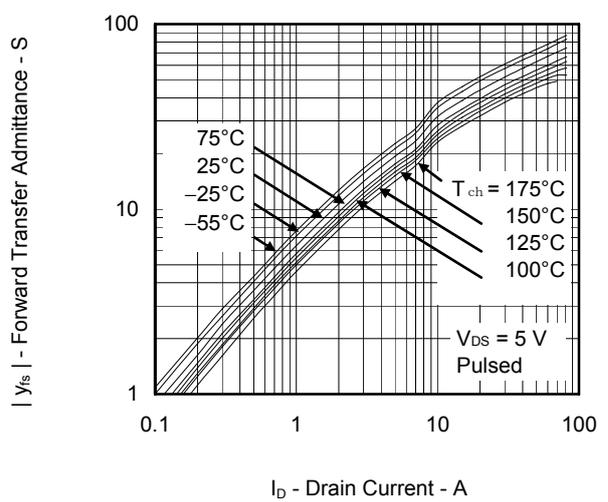
FORWARD TRANSFER CHARACTERISTICS



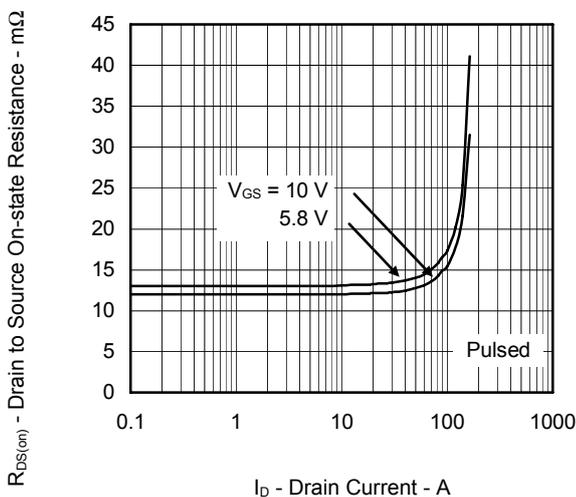
GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE



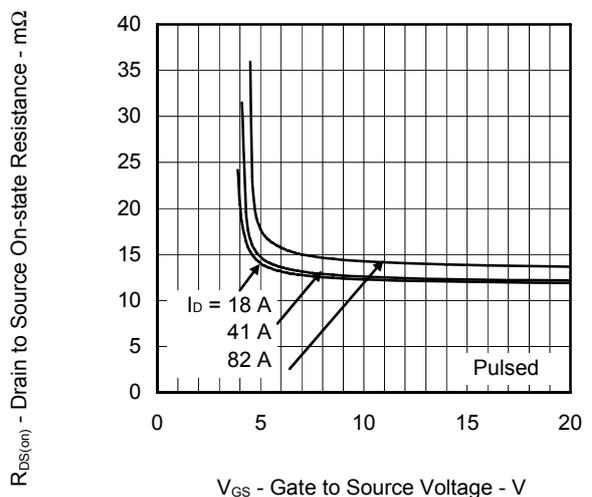
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



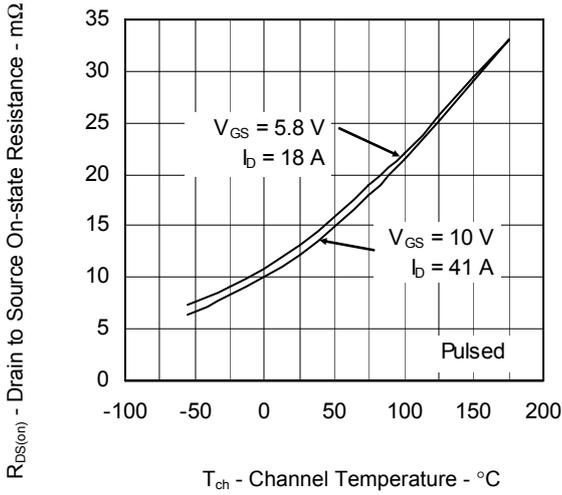
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



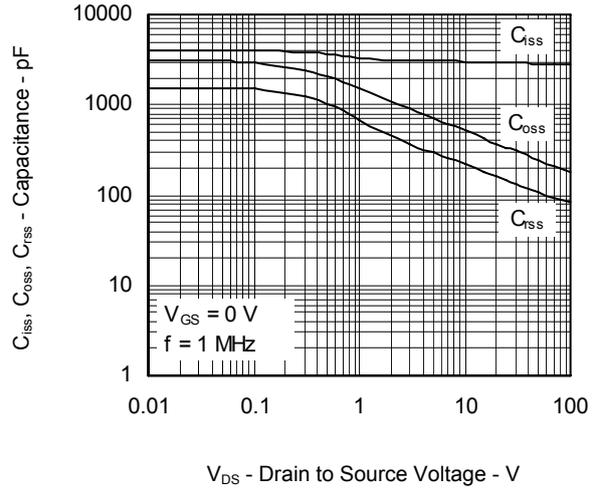
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



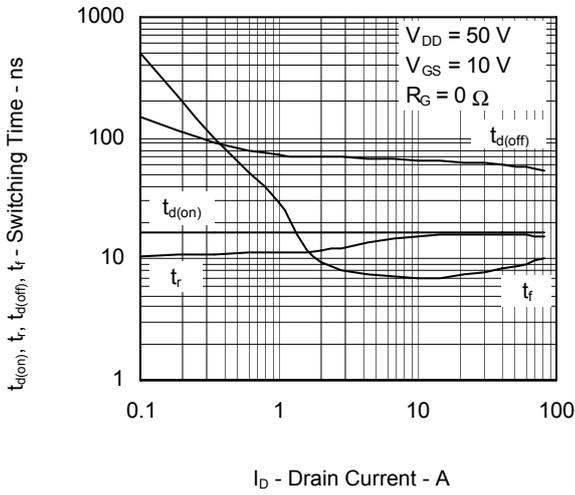
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



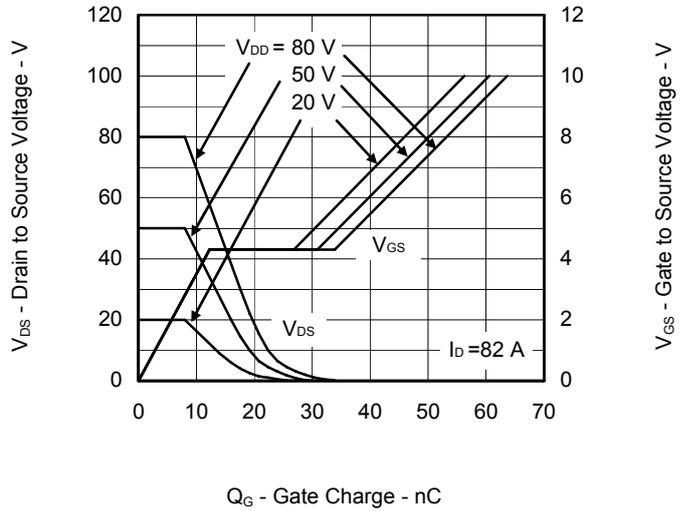
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



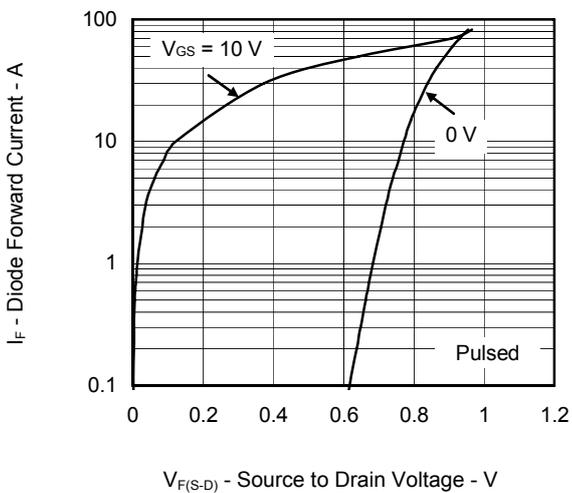
SWITCHING CHARACTERISTICS



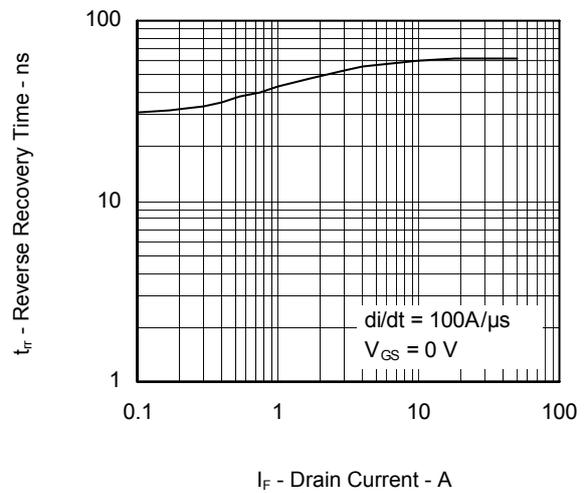
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

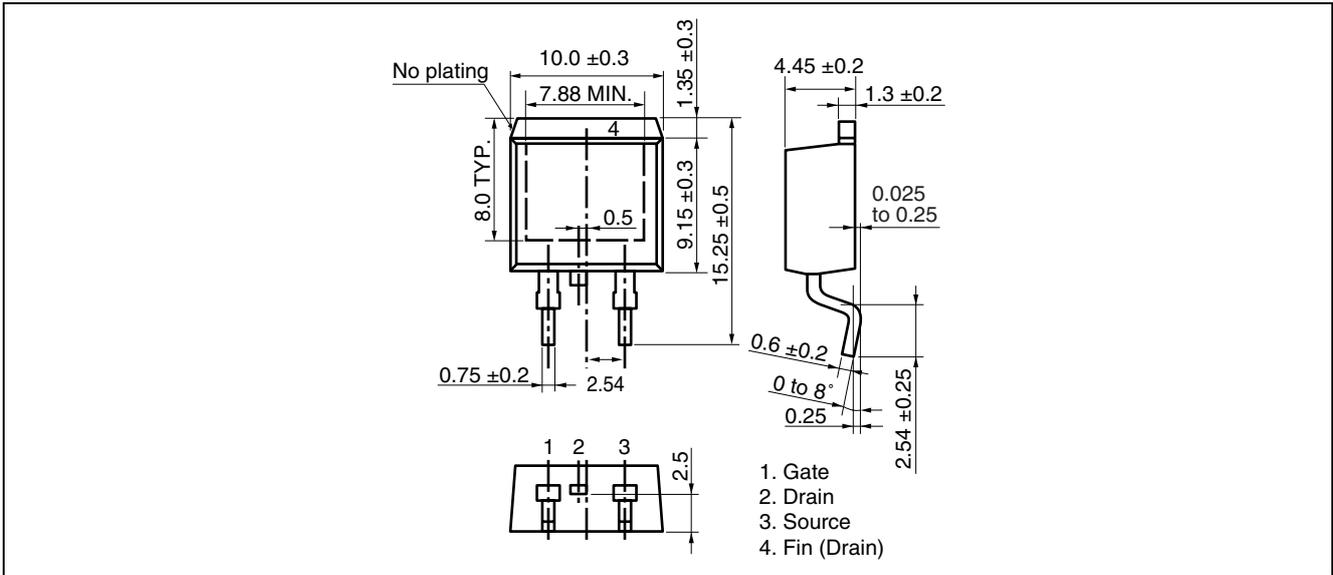


REVERSE RECOVERY TIME vs. DRAIN CURRENT

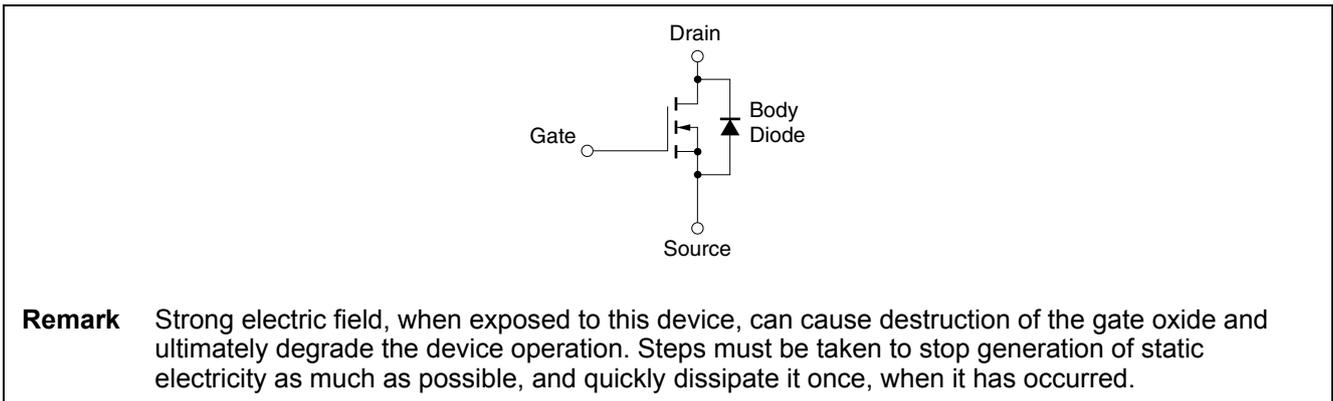


Package Drawings (Unit: mm)

TO-263 (MP-25ZP) (Mass: 1.5 g TYP.)



Equivalent Circuit



Revision History	NP82N10PUF Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Aug 26, 2011	-	First Edition Issued

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